



100V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -100V
- I_C = -5A High Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -115mV @ -1A
- R_{CE(SAT)} = 75mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified up to -10A for a High Gain Hold-Up
- Complementary NPN Type: FZT853
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

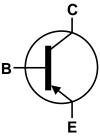
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

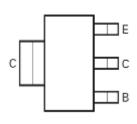




Top View



Device Symbol



Top View Pin-Out

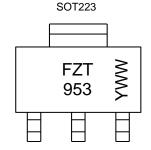
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT953TA	AEC-Q101	FZT953	7	12	1,000
FZT953QTA	Automotive	FZT953	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



FZT 953 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 7 = 2017) WW or $\overline{W}W$ = Week Code (01–53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Peak Pulse Current	Ісм	-10	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)		3.0 24	W mW /°C
Linear Derating Factor	(Note 7)	P_{D}	1.6 12.8	
Thermal Desistance Junation to Ambient	(Note 6)	R _{0JA}	42	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	78	°C/W
Thermal Resistance Junction to Lead	(Note 8)	$R_{\theta JL}$	8.84	
Operating and Storage Temperature Range	<u>.</u>	$T_{J_i}T_{STG}$	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes:

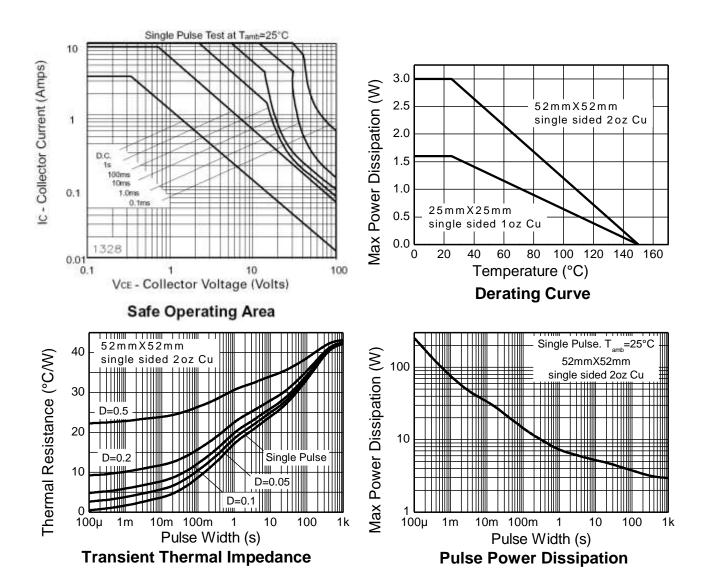
6. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

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- 7. Same as Note 6, except the device is surface mounted on 25mm x 25mm with 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-140	-170	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CER}	-140	-170	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-100	-120	_	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	_	<-1 —	-50 -1	nΑ μΑ	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Collector Cutoff Current	I _{CER}	_	<-1 —	-50 -1	nΑ μΑ	$V_{CE} = -100V$, R ≤ 1kΩ $V_{CE} = -100V$, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	_	<-1	-10	nA	V _{EB} = -6V
		100	200	_		$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
	h _{FE}	100	200	300	_	$I_{C} = -1A, V_{CE} = -1V$
DC Current Transfer Static Ratio (Note 10)		50	90	_		$I_C = -3A$, $V_{CE} = -1V$
		30	50	_		$I_C = -4A$, $V_{CE} = -1V$
		_	15	_		$I_C = -10A$, $V_{CE} = -1V$
	V _{CE} (SAT)	_	-20	-50	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)		_	-90	-115		$I_C = -1A$, $I_B = -100mA$
Collector-Entitle Saturation voltage (Note 10)		_	-160	-220		$I_C = -2A$, $I_B = -200mA$
		_	-300	-420		$I_C = -4A$, $I_B = -400mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	-1,010	-1,170	mV	$I_C = -4A$, $I_B = -400mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	_	-925	-1,160	mV	$I_C = -4A$, $V_{CE} = -1V$
Transitional Frequency	f _T	_	125	_	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50 MHz
Output Capacitance	C_{OBO}	_	65	_	pF	$V_{CB} = -10V$, $f = 1MHz$
Switching Time	toN	_	110	_	ne	$V_{CC} = -10V, I_C = -2A,$
Switching Time	toff	_	460	_	ns	$-I_{B1} = I_{B2} = -200 \text{mA}$

Note:

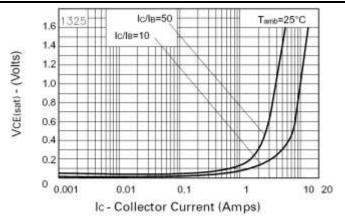
10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

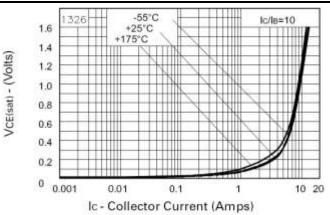
lc/le=10

10 20



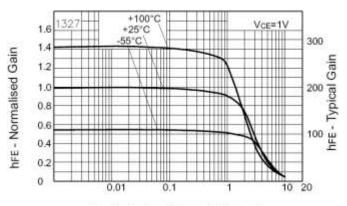
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





VCE(sat) v IC

VCE(sat) v IC



+100°C +175°C 1.4 1.2 1.0 0.8 0.6 0.4 0.2 0

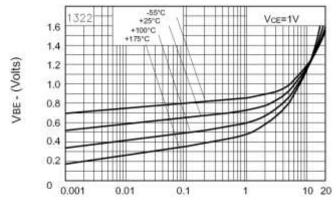
1.6

0.001

VBE(sat) - (Volts)

Ic - Collector Current (Amps)

hFE v lc



Ic - Collector Current (Amps)

VBE(on) v IC

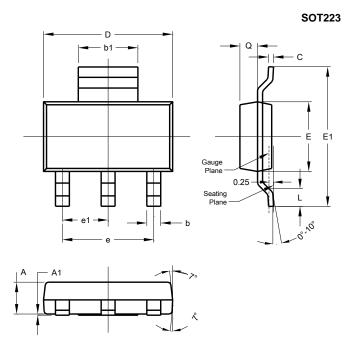
Ic - Collector Current (Amps) VBE(sat) v IC

0.1



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

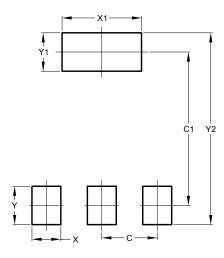


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
V2	8 00		



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